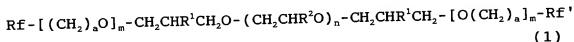


CLAIMS:

- sub B1
1. A resist composition comprising a fluorochemical surfactant which functions to reduce the contact angle at the interface between the surface of the resist composition coated onto a substrate and water or an aqueous base developer as the amount of the fluorochemical surfactant increases.

- 10 2. The resist composition of claim 1 wherein said fluorochemical surfactant is of the following general formula (1):



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- wherein R¹ is hydrogen, a hydroxyl group, a straight, branched or cyclic alkoxy group of 1 to 6 carbon atoms, or an alkylcarbonyloxy group whose alkyl moiety has 1 to 6 carbon atoms, R² is hydrogen or a straight, branched or cyclic alkyl group of 1 to 6 carbon atoms, a is a positive integer of 0 to 6, m is equal to 0 or 1, and n is a positive integer of 1 to 40, each of Rf and Rf', which may be the same or different, is a straight, branched or cyclic fluoroalkyl group having 1 to 12 carbon atoms, in which all groups attached to its carbon atoms are fluorine atoms or some are fluorine atoms and the remainder are hydrogen atoms.

- 30 3. The resist composition of claim 1 which is of chemical amplification type and to be exposed to high-energy radiation having a wavelength of 500 nm or less, x-rays or electron beams.

- 35 4. A method for forming a resist pattern comprising the steps of:

(i) coating a resist composition according to claim 3 onto a substrate,

(ii) heat treating the coated film and then exposing it to high-energy radiation having a wavelength of 500 nm or less, x-rays or electron beams through a photo mask, and

(iii) optionally heat treating the exposed film and developing it with a developer.

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